IN THE DRAWINGS

The drawings were objected to under 37 CFR 1.83(a). The objection stated: "The drawings must show every feature of the invention specified in the claims. Therefore, the complete process step of reducing the channel length while the side of the gate dielectric exposed must be shown or the feature(s) canceled from the claim(s). No new matter should be entered."

Applicant respectfully submits that the drawings show every feature of the invention specified in the claims to be sufficient under 37 CFR 1.83(a). Figure 3C and 3D, for example, illustrate one embodiment including reducing a physical gate width 362 while the side of the gate dielectric 310 is exposed as shown in the figures. Figure 3C is further discussed in the specification on page 7 in the second paragraph.

> As the material in the gate 330 is consumed, the side dielectric regions 366 and 368 define a new physical gate width 362. The process of creating the side dielectric regions 366 and 368 is a controlled process, and as a result, the physical gate width 362 can be adjusted to a high degree of accuracy. This is advantageous because the physical gate width affects the Leff of the transistor 301.

Reconsideration and withdrawal of the objection is respectfully requested.